



SANYO Semiconductors

# DATA SHEET

## 2SK2628FS — N-Channel Silicon MOSFET General-Purpose Switching Device Applications

### Features

- Low ON-resistance.
- Low Qg.
- Ultrahigh-speed switching.

### Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V <sub>DSS</sub>		600	V
Gate-to-Source Voltage	V <sub>GSS</sub>		±30	V
Drain Current (DC)	I <sub>DC</sub> *1	Limited only by maximum temperature	7	A
	I <sub>Dpack</sub> *2	Tc=25°C (SANYO's ideal heat dissipation condition)*3	6.2	A
Drain Current (Pulse)	I <sub>DP</sub>	PW≤10μs, duty cycle≤1%	24	A
			2.0	W
Allowable Power Dissipation	PD	Tc=25°C (SANYO's ideal heat dissipation condition)*3	35	W
			150	°C
Channel Temperature	T <sub>ch</sub>			
Storage Temperature	T <sub>stg</sub>		-55 to +150	°C
Avalanche Energy (Single Pulse) *4	E <sub>AS</sub>		98	mJ
Avalanche Current *5	I <sub>AV</sub>		6	A

Note : \*1 Shows chip capability

\*2 Package limited

\*3 SANYO's condition is radiation from backside.

The method is applying silicone grease to the backside of the device and attaching the device to water-cooled radiator made of aluminium.

\*4 V<sub>DD</sub>=50V, L=5mH, I<sub>AV</sub>=6A

\*5 L≤5mH, Single pulse

Marking : K2628

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# 2SK2628FS

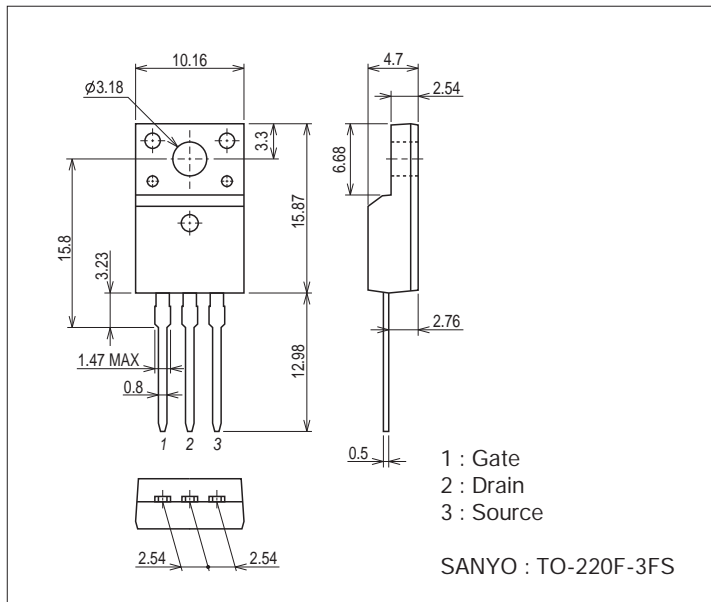
## Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D=10mA, V_{GS}=0V$	600			V
Zero-Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=480V, V_{GS}=0V$			1.0	mA
Gate-to-Source Leakage Current	$I_{GSS}$	$V_{GS}=\pm 30V, V_{DS}=0V$			$\pm 100$	nA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS}=10V, I_D=1mA$	3.5		5.5	V
Forward Transfer Admittance	$ y_{fs} $	$V_{DS}=10V, I_D=4A$	2.0	4.0		S
Static Drain-to-Source On-State Resistance	$R_{DS(on)}$	$I_D=2A, V_{GS}=15V$		0.9	1.1	$\Omega$
Input Capacitance	$C_{iss}$	$V_{DS}=20V, f=1MHz$		1050		pF
Output Capacitance	$C_{oss}$	$V_{DS}=20V, f=1MHz$		320		pF
Reverse Transfer Capacitance	$C_{rss}$	$V_{DS}=20V, f=1MHz$		180		pF
Turn-ON Delay Time	$t_d(on)$	See specified Test Circuit.		23		ns
Rise Time	$t_r$	See specified Test Circuit.		35		ns
Turn-OFF Delay Time	$t_d(off)$	See specified Test Circuit.		90		ns
Fall Time	$t_f$	See specified Test Circuit.		35		ns
Total Gate Charge	$Q_g$	$V_{DS}=200V, V_{GS}=10V, I_D=6A$		30		nC
Diode Forward Voltage	$V_{SD}$	$I_S=6A, V_{GS}=0V$		0.85	1.2	V

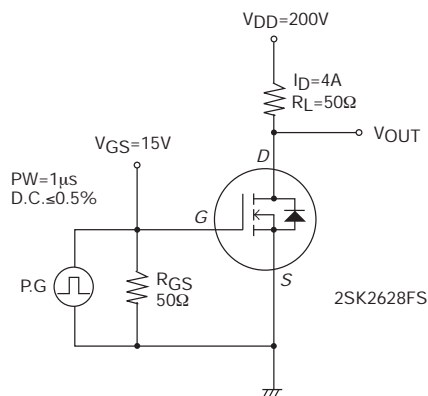
## Package Dimensions

unit : mm (typ)

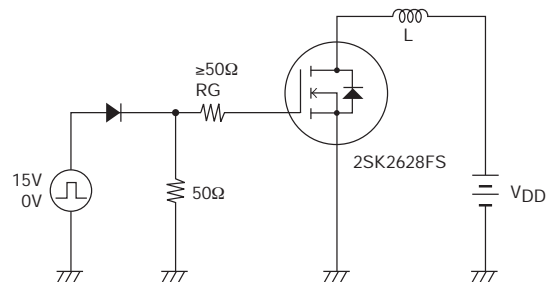
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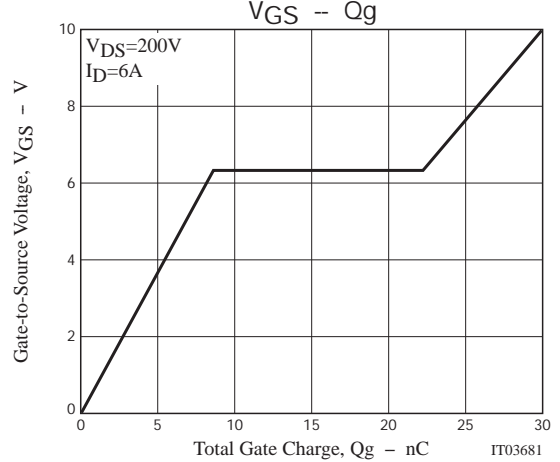
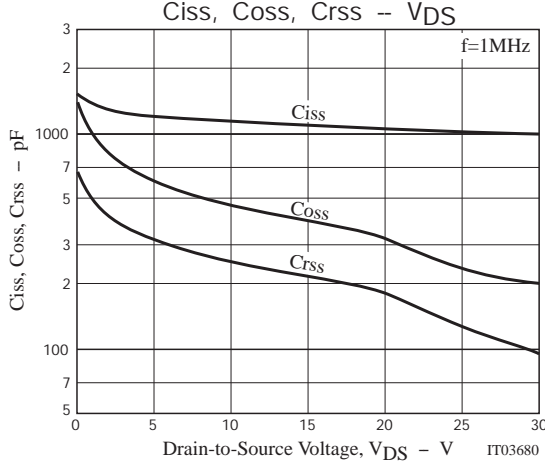
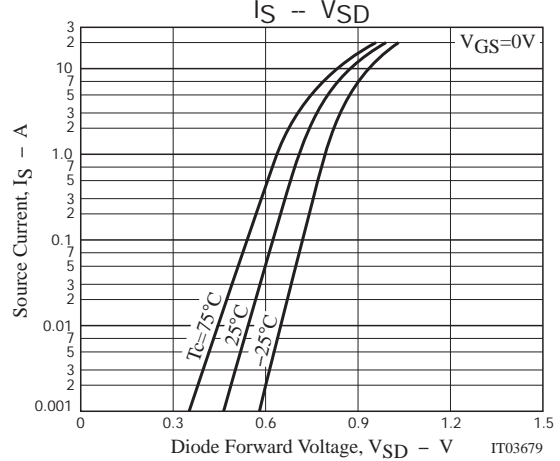
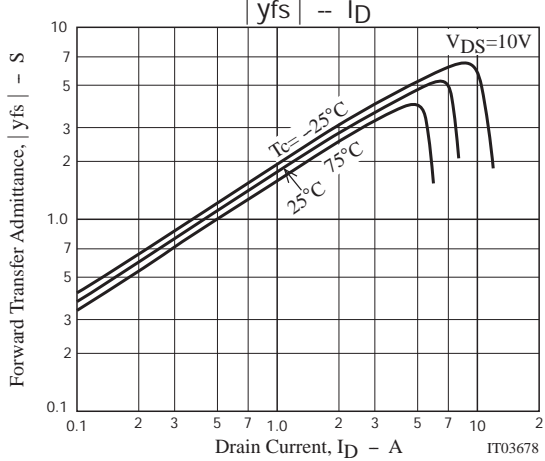
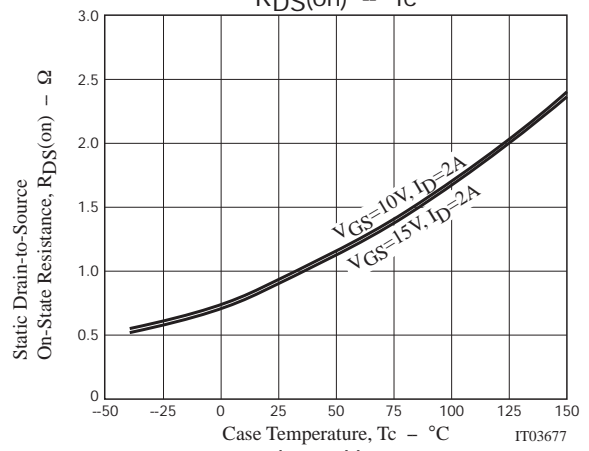
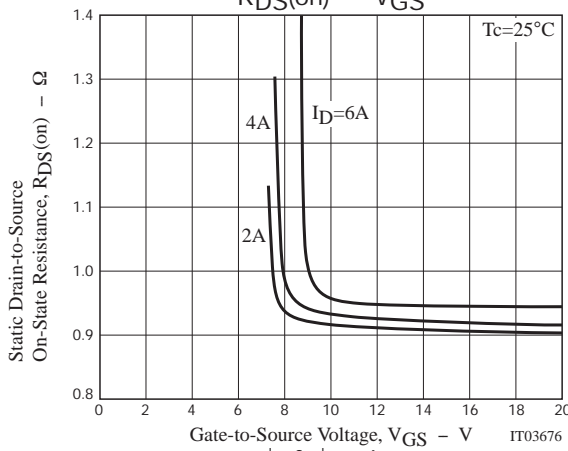
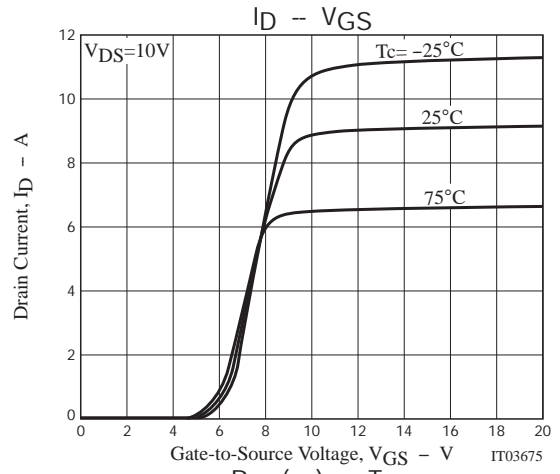
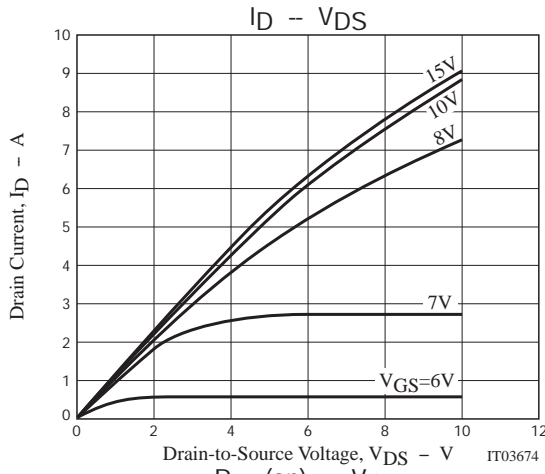


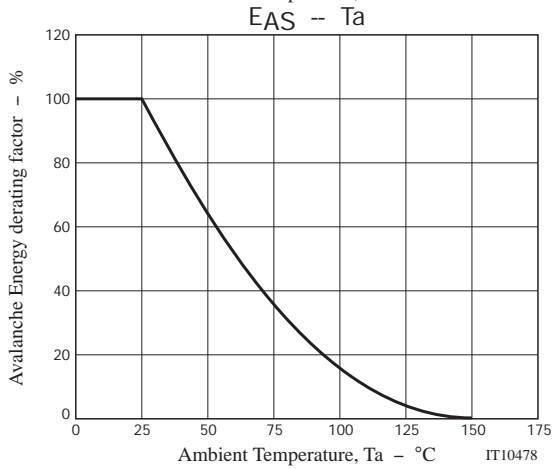
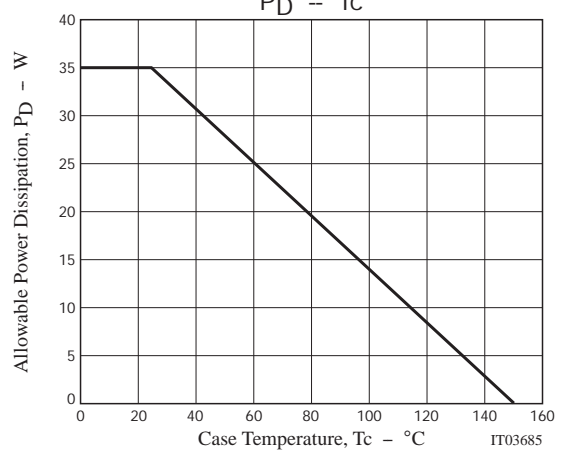
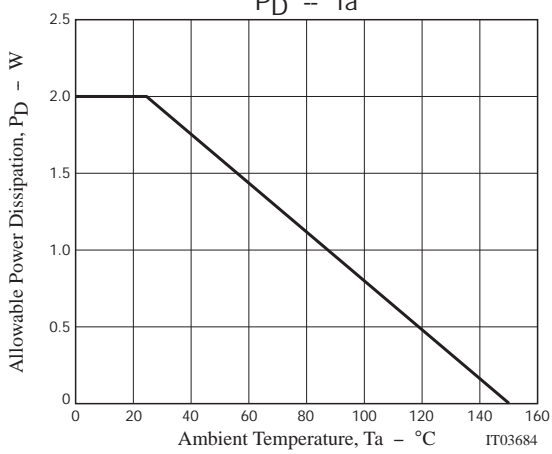
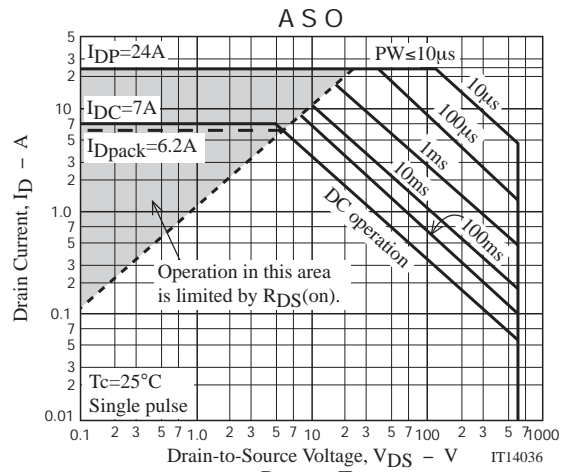
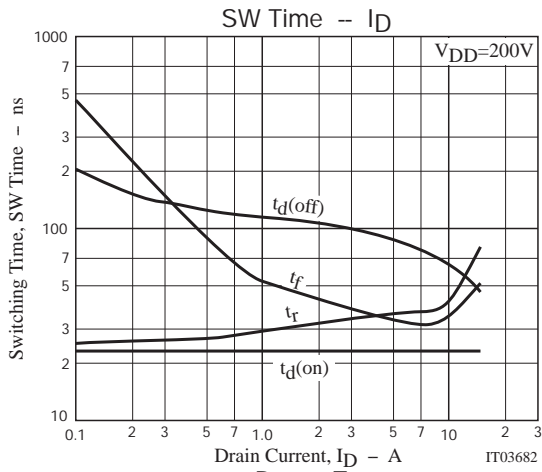
## Switching Time Test Circuit



## Avalanche Resistance Test Circuit







Note on usage : Since the 2SK2628FS is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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